

# Edward T Yu

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2346963/publications.pdf>

Version: 2024-02-01

235  
papers

11,294  
citations

34016

52  
h-index

32761

100  
g-index

236  
all docs

236  
docs citations

236  
times ranked

11243  
citing authors

| #  | ARTICLE   | IF   | CITATIONS |
|----|---|------|-----------|
| 1  | Enhanced semiconductor optical absorption via surface plasmon excitation in metal nanoparticles. Applied Physics Letters, 2005, 86, 063106.   | 1.5  | 1,043     |
| 2  | Improved performance of amorphous silicon solar cells via scattering from surface plasmon polaritons in nearby metallic nanoparticles. Applied Physics Letters, 2006, 89, 093103.   | 1.5  | 715       |
| 3  | A silicon-based photocathode for water reduction with an epitaxial SrTiO <sub>3</sub> protection layer and a nanostructured catalyst. Nature Nanotechnology, 2015, 10, 84-90.   | 15.6 | 353       |
| 4  | Measurement of piezoelectrically induced charge in GaN/AlGa <sub>N</sub> heterostructure field-effect transistors. Applied Physics Letters, 1997, 71, 2794-2796.  | 1.5  | 336       |
| 5  | Photocurrent spectroscopy of optical absorption enhancement in silicon photodiodes via scattering from surface plasmon polaritons in gold nanoparticles. Journal of Applied Physics, 2007, 101, 104309.   | 1.1  | 327       |
| 6  | High Electron Mobility InAs Nanowire Field-Effect Transistors. Small, 2007, 3, 326-332.   | 5.2  | 293       |
| 7  | Analysis of leakage current mechanisms in Schottky contacts to GaN and Al <sub>0.25</sub> Ga <sub>0.75</sub> N <sup>δ</sup> -GaN grown by molecular-beam epitaxy. Journal of Applied Physics, 2006, 99, 023703.   | 1.1  | 283       |
| 8  | Analysis of reverse-bias leakage current mechanisms in GaN grown by molecular-beam epitaxy. Applied Physics Letters, 2004, 84, 535-537.   | 1.5  | 257       |
| 9  | Piezoelectric charge densities in AlGa <sub>N</sub> /GaN HFETs. Electronics Letters, 1997, 33, 1230.  | 0.5  | 253       |
| 10 | Metal and dielectric nanoparticle scattering for improved optical absorption in photovoltaic devices. Applied Physics Letters, 2008, 93, 113108.  | 1.5  | 243       |
| 11 | Correlated scanning Kelvin probe and conductive atomic force microscopy studies of dislocations in gallium nitride. Journal of Applied Physics, 2003, 94, 1448-1453.  | 1.1  | 190       |
| 12 | Precise Semiconductor Nanowire Placement Through Dielectrophoresis. Nano Letters, 2009, 9, 2260-2266.   | 4.5  | 188       |
| 13 | Gate leakage current mechanisms in AlGa <sub>N</sub> /GaN heterostructure field-effect transistors. Journal of Applied Physics, 2000, 88, 5951-5958.  | 1.1  | 184       |
| 14 | Spontaneous and piezoelectric polarization effects in III <sup>δ</sup> -V nitride heterostructures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1742. | 1.6  | 180       |
| 15 | Multiband treatment of quantum transport in interband tunnel devices. Physical Review B, 1992, 45, 3583-3592.   | 1.1  | 170       |
| 16 | III <sup>δ</sup> -V Nanowire Growth Mechanism: V/III Ratio and Temperature Effects. Nano Letters, 2007, 7, 2486-2490.   | 4.5  | 166       |
| 17 | InP Nanowire/Polymer Hybrid Photodiode. Nano Letters, 2008, 8, 775-779.   | 4.5  | 166       |
| 18 | Nanoparticle-induced light scattering for improved performance of quantum-well solar cells. Applied Physics Letters, 2008, 93, 091107.  | 1.5  | 134       |

| #  | ARTICLE   | IF  | CITATIONS |
|----|---|-----|-----------|
| 19 | Critical dimensions in coherently strained coaxial nanowire heterostructures. Journal of Applied Physics, 2006, 99, 114308.   | 1.1 | 133       |
| 20 | Schottky barrier engineering in III-V nitrides via the piezoelectric effect. Applied Physics Letters, 1998, 73, 1880-1882.  | 1.5 | 130       |
| 21 | Measurement of polarization charge and conduction-band offset at In <sub>x</sub> Ga <sub>1-x</sub> N/GaN heterojunction interfaces. Applied Physics Letters, 2004, 84, 4644-4646.                           | 1.5 | 126       |
| 22 | Deep level defects in n-type GaN grown by molecular beam epitaxy. Applied Physics Letters, 1998, 72, 1211-1213.   | 1.5 | 123       |
| 23 | Highly Controllable and Stable Quantized Conductance and Resistive Switching Mechanism in Single-Crystal TiO <sub>2</sub> Resistive Memory on Silicon. Nano Letters, 2014, 14, 4360-4367.                   | 4.5 | 121       |
| 24 | Design of Tunneling Field-Effect Transistors Based on Staggered Heterojunctions for Ultralow-Power Applications. IEEE Electron Device Letters, 2010, 31, 431-433.   | 2.2 | 116       |
| 25 | Influence of surface states on the extraction of transport parameters from InAs nanowire field effect transistors. Applied Physics Letters, 2007, 90, 1621-1622.  | 1.5 | 112       |
| 26 | Trap characterization by gate-drain conductance and capacitance dispersion studies of an AlGaIn/GaN heterostructure field-effect transistor. Journal of Applied Physics, 2000, 87, 8070-8073.               | 1.1 | 111       |
| 27 | Charge storage in Co nanoclusters embedded in SiO <sub>2</sub> by scanning force microscopy. Applied Physics Letters, 1999, 74, 472-474.  | 1.5 | 109       |
| 28 | Band Offsets in Semiconductor Heterojunctions. Solid State Physics, 1992, , 1-146.  | 1.3 | 98        |
| 29 | Integrated One Diode-One Resistor Architecture in Nanopillar SiO <sub>2</sub> Resistive Switching Memory by Nanosphere Lithography. Nano Letters, 2014, 14, 813-818.  | 4.5 | 97        |
| 30 | Out-of-Plane Electromechanical Response of Monolayer Molybdenum Disulfide Measured by Piezoresponse Force Microscopy. Nano Letters, 2017, 17, 5464-5471.  | 4.5 | 94        |
| 31 | Reduction of reverse-bias leakage current in Schottky diodes on GaN grown by molecular-beam epitaxy using surface modification with an atomic force microscope. Journal of Applied Physics, 2002, 91, 9821. | 1.1 | 93        |
| 32 | Measurement of drift mobility in AlGaIn/GaN heterostructure field-effect transistor. Applied Physics Letters, 1999, 74, 3890-3892.  | 1.5 | 89        |
| 33 | Cross-sectional imaging and spectroscopy of GaAs doping superlattices by scanning tunneling microscopy. Applied Physics Letters, 1992, 61, 795-797.   | 1.5 | 88        |
| 34 | Structural and Room-Temperature Transport Properties of Zinc Blende and Wurtzite InAs Nanowires. Advanced Functional Materials, 2009, 19, 2102-2108.  | 7.8 | 86        |
| 35 | Interface Adhesion between 2D Materials and Elastomers Measured by Buckle Delaminations. Advanced Materials Interfaces, 2015, 2, 1500176.   | 1.9 | 85        |
| 36 | Direct observation of ballistic and drift carrier transport regimes in InAs nanowires. Applied Physics Letters, 2006, 89, 053113.   | 1.5 | 78        |

| #  | ARTICLE  | IF   | CITATIONS |
|----|--|------|-----------|
| 37 | Persistent photoconductivity and defect levels in n-type AlGaIn/GaN heterostructures. Applied Physics Letters, 1998, 72, 2745-2747.  | 1.5  | 75        |
| 38 | Transport properties of InAs nanowire field effect transistors: The effects of surface states. Journal of Vacuum Science & Technology B, 2007, 25, 1432.   | 1.3  | 74        |
| 39 | Surface Diffusion and Substrate-Nanowire Adatom Exchange in InAs Nanowire Growth. Nano Letters, 2009, 9, 1967-1972.  | 4.5  | 71        |
| 40 | Electrodeposition of crystalline silicon films from silicon dioxide for low-cost photovoltaic applications. Nature Communications, 2019, 10, 5772.   | 5.8  | 70        |
| 41 | Scanning tunneling spectroscopy and Kelvin probe force microscopy investigation of Fermi energy level pinning mechanism on InAs and InGaAs clean surfaces. Journal of Applied Physics, 2010, 108, .                      | 1.1  | 69        |
| 42 | Toward Cost-Effective Manufacturing of Silicon Solar Cells: Electrodeposition of High-Quality Si Films in a CaCl <sub>2</sub> -based Molten Salt. Angewandte Chemie - International Edition, 2017, 56, 15078-15082.      | 7.2  | 66        |
| 43 | Transport Coefficients of InAs Nanowires as a Function of Diameter. Small, 2009, 5, 77-81.   | 5.2  | 63        |
| 44 | Photon management for photovoltaics. MRS Bulletin, 2011, 36, 424-428.  | 1.7  | 63        |
| 45 | In <sub>0.5</sub> Cd <sub>0.5</sub> Se/ZnTe based wide band-gap light emitters: Numerical simulation and design. Journal of Applied Physics, 1993, 73, 4660-4668.  | 1.1  | 62        |
| 46 | Localized dielectric breakdown and antireflection coating in metal-oxide-semiconductor photoelectrodes. Nature Materials, 2017, 16, 127-131.   | 13.3 | 60        |
| 47 | Cross-Sectional Scanning Tunneling Microscopy of Semiconductor Heterostructures. MRS Bulletin, 1997, 22, 22-26.  | 1.7  | 59        |
| 48 | Piezoelectric polarization associated with dislocations in wurtzite GaN. Applied Physics Letters, 1999, 74, 573-575.   | 1.5  | 59        |
| 49 | Lateral variations in threshold voltage of an Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN heterostructure field-effect transistor measured by scanning capacitance spectroscopy. Applied Physics Letters, 2001, 78, 88-90.   | 1.5  | 59        |
| 50 | Epitaxial c-axis oriented BaTiO <sub>3</sub> thin films on SrTiO <sub>3</sub> -buffered Si(001) by atomic layer deposition. Applied Physics Letters, 2014, 104, .  | 1.5  | 59        |
| 51 | Influence of surface processing and passivation on carrier concentrations and transport properties in AlGaIn/GaN heterostructures. Journal of Applied Physics, 2001, 90, 1357-1361.                                      | 1.1  | 56        |
| 52 | Electrochemical Formation of a p-n Junction on Thin Film Silicon Deposited in Molten Salt. Journal of the American Chemical Society, 2017, 139, 16060-16063.   | 6.6  | 56        |
| 53 | A Liquid Junction Photoelectrochemical Solar Cell Based on p-Type MeNH <sub>3</sub> PbI <sub>3</sub> Perovskite with 1.05 V Open-Circuit Photovoltage. Journal of the American Chemical Society, 2015, 137, 14758-14764. | 6.6  | 52        |
| 54 | X-ray photoelectron spectroscopy measurement of valence-band offsets for Mg-based semiconductor compounds. Applied Physics Letters, 1994, 64, 3455-3457.   | 1.5  | 50        |

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 55 | Optimization of $\text{PbI}_2/\text{MAPbI}_3$ Perovskite Composites by Scanning Electrochemical Microscopy. <i>Journal of Physical Chemistry C</i> , 2016, 120, 19890-19895.   | 1.5 | 50        |
| 56 | Reverse-bias leakage current reduction in GaN Schottky diodes by electrochemical surface treatment. <i>Applied Physics Letters</i> , 2003, 82, 1293-1295.  | 1.5 | 49        |
| 57 | Measurement of the valence band offset in strained Si/Ge(100) heterojunctions by x-ray photoelectron spectroscopy. <i>Applied Physics Letters</i> , 1990, 56, 569-571.   | 1.5 | 48        |
| 58 | Anisotropy and growth-sequence dependence of atomic-scale interface structure in InAs/Ga $_{1-x}$ In $_x$ Sb superlattices. <i>Applied Physics Letters</i> , 1997, 70, 75-77.  | 1.5 | 48        |
| 59 | Optimization of Lead-free Organic-Inorganic Tin(II) Halide Perovskite Semiconductors by Scanning Electrochemical Microscopy. <i>Electrochimica Acta</i> , 2016, 220, 205-210.  | 2.6 | 47        |
| 60 | Calculation of critical dimensions for wurtzite and cubic zinc blende coaxial nanowire heterostructures. <i>Journal of Vacuum Science &amp; Technology B</i> , 2006, 24, 2053.   | 1.3 | 46        |
| 61 | Electrical profiling of Si(001) pn junctions by scanning tunneling microscopy. <i>Applied Physics Letters</i> , 1992, 61, 201-203.   | 1.5 | 45        |
| 62 | Direct measurement of the polarization charge in AlGa $_x$ N/GaN heterostructures using capacitance-voltage carrier profiling. <i>Applied Physics Letters</i> , 2002, 80, 3551-3553.   | 1.5 | 44        |
| 63 | Experimental realization and modeling of a subwavelength frequency-selective plasmonic metasurface. <i>Applied Physics Letters</i> , 2011, 99, .   | 1.5 | 44        |
| 64 | Measurement of the CdSe/ZnTe valence band offset by x-ray photoelectron spectroscopy. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1991, 9, 2233. | 1.6 | 43        |
| 65 | Scanning Kelvin probe microscopy of surface electronic structure in GaN grown by hydride vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2002, 91, 9924.  | 1.1 | 43        |
| 66 | Atomic layer deposition of crystalline SrHfO $_3$ directly on Ge (001) for high- $k$ dielectric applications. <i>Journal of Applied Physics</i> , 2015, 117, .   | 1.1 | 43        |
| 67 | Improved Performance of Zinc Oxide Thin Film Transistor Pressure Sensors and a Demonstration of a Commercial Chip Compatibility with the New Force Sensing Technology. <i>Advanced Materials Technologies</i> , 2018, 3, 1700279.                        | 3.0 | 43        |
| 68 | Hole tunneling times in GaAs/AlAs double-barrier structures. <i>Applied Physics Letters</i> , 1989, 55, 744-746.   | 1.5 | 42        |
| 69 | Role of heavy-hole states in interband tunnel structures. <i>Applied Physics Letters</i> , 1991, 58, 292-294.  | 1.5 | 42        |
| 70 | Large peak current densities in novel resonant interband tunneling heterostructures. <i>Applied Physics Letters</i> , 1990, 57, 1257-1259.   | 1.5 | 41        |
| 71 | Experimental observation of negative differential resistance from an InAs/GaSb interface. <i>Applied Physics Letters</i> , 1990, 57, 683-685.  | 1.5 | 40        |
| 72 | A Chemical Route to Monolithic Integration of Crystalline Oxides on Semiconductors. <i>Advanced Materials Interfaces</i> , 2014, 1, 1400081.   | 1.9 | 40        |

| #  | ARTICLE  | IF   | CITATIONS |
|----|--|------|-----------|
| 73 | Cross-Sectional Scanning Tunneling Microscopy. Chemical Reviews, 1997, 97, 1017-1044.  | 23.0 | 39        |
| 74 | Modeling of novel heterojunction tunnel structures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1990, 8, 810.  | 1.6  | 38        |
| 75 | Growth of InAs Nanowires on SiO <sub>2</sub> Substrates: Nucleation, Evolution, and the Role of Au Nanoparticles. Journal of Physical Chemistry C, 2007, 111, 13331-13336.   | 1.5  | 38        |
| 76 | Light trapping in thin-film solar cells via scattering by nanostructured antireflection coatings. Journal of Applied Physics, 2013, 114, 044310.   | 1.1  | 38        |
| 77 | Fabrication and characterisation of enhanced barrier AlGaIn/GaN HFET. Electronics Letters, 1999, 35, 602.  | 0.5  | 37        |
| 78 | Origin and microscopic mechanism for suppression of leakage currents in Schottky contacts to GaN grown by molecular-beam epitaxy. Journal of Applied Physics, 2003, 94, 7611.  | 1.1  | 37        |
| 79 | Enhancement of base conductivity via the piezoelectric effect in AlGaIn/GaN HBTs. Solid-State Electronics, 2000, 44, 211-219.  | 0.8  | 36        |
| 80 | Low defect-mediated reverse-bias leakage in (0001) GaN via high-temperature molecular beam epitaxy. Applied Physics Letters, 2010, 96, .   | 1.5  | 35        |
| 81 | Measurement of the valence band offset in novel heterojunction systems: Si/Ge (100) and AlSb/ZnTe (100). Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1990, 8, 908. | 1.6  | 34        |
| 82 | Demonstration of resonant transmission in InAs/GaSb/InAs interband tunneling devices. Applied Physics Letters, 1990, 57, 2675-2677.  | 1.5  | 33        |
| 83 | Field Dependent Transport Properties in InAs Nanowire Field Effect Transistors. Nano Letters, 2008, 8, 3114-3119.  | 4.5  | 33        |
| 84 | Plasmonic nanoparticle scattering for enhanced performance of photovoltaic and photodetector devices. Proceedings of SPIE, 2008, , .   | 0.8  | 33        |
| 85 | Excess Indium and Substrate Effects on the Growth of InAs Nanowires. Small, 2007, 3, 1683-1687.  | 5.2  | 31        |
| 86 | High ON/OFF Ratio and Quantized Conductance in Resistive Switching of $\text{TiO}_2$ on Silicon. IEEE Electron Device Letters, 2013, 34, 1385-1387.  | 2.2  | 31        |
| 87 | Asymmetric light reflectance from metal nanoparticle arrays on dielectric surfaces. Scientific Reports, 2015, 5, 18331.  | 1.6  | 31        |
| 88 | Oxygen-induced bi-modal failure phenomenon in SiOx-based resistive switching memory. Applied Physics Letters, 2013, 103, 033521.   | 1.5  | 30        |
| 89 | Scanning tunneling microscopy of InAs/Ga <sub>1-x</sub> In <sub>x</sub> Sb superlattices. Applied Physics Letters, 1994, 65, 201-203.  | 1.5  | 29        |
| 90 | Nanoscale characterization of semiconductor materials and devices using scanning probe techniques. Materials Science and Engineering Reports, 1996, 17, 147-206.   | 14.8 | 29        |

| #   | ARTICLE   | IF  | CITATIONS |
|-----|---|-----|-----------|
| 91  | Two-dimensional profiling of shallow junctions in Si metal-oxide-semiconductor structures using scanning tunneling spectroscopy and transmission electron microscopy. Journal of Applied Physics, 1996, 79, 2115-2121.  | 1.1 | 28        |
| 92  | Band offsets in Si/Si <sub>1-x</sub> Ge <sub>x</sub> heterojunctions measured by admittance spectroscopy. Applied Physics Letters, 1997, 70, 3413-3415.   | 1.5 | 28        |
| 93  | III-V double-barrier resonant tunneling structures. Applied Physics Letters, 1988, 53, 60-62.   | 1.5 | 27        |
| 94  | Characterization of Al <sub>x</sub> Ga <sub>1-x</sub> As/GaAs heterojunction bipolar transistor structures using cross-sectional scanning force microscopy. Journal of Applied Physics, 2000, 87, 1937-1942.  | 1.1 | 27        |
| 95  | Improved performance of In(Ga)As/GaAs quantum dot solar cells via light scattering by nanoparticles. Journal of Applied Physics, 2009, 106, .   | 1.1 | 27        |
| 96  | Investigation of edge- and bulk-related resistive switching behaviors and backward-scan effects in SiO <sub>2</sub> -based resistive switching memory. Applied Physics Letters, 2013, 103, 193508.  | 1.5 | 26        |
| 97  | Zeta Potential Dependent Self-Assembly for Very Large Area Nanosphere Lithography. Nano Letters, 2020, 20, 5090-5096.   | 4.5 | 26        |
| 98  | Scanning capacitance microscopy of AlGaN/GaN heterostructure field-effect transistor epitaxial layer structures. Applied Physics Letters, 1999, 75, 2250-2252.  | 1.5 | 25        |
| 99  | Correlation between atomic-scale structure and mobility anisotropy in InAs/Ga <sub>1-x</sub> In <sub>x</sub> Sb superlattices. Physical Review B, 1998, 57, 6534-6539.  | 1.1 | 24        |
| 100 | Electrochemical Monitoring of TiO <sub>2</sub> Atomic Layer Deposition by Chronoamperometry and Scanning Electrochemical Microscopy. Chemistry of Materials, 2013, 25, 4165-4172.   | 3.2 | 24        |
| 101 | Epitaxial ALD BeO: Efficient Oxygen Diffusion Barrier for EOT Scaling and Reliability Improvement. IEEE Transactions on Electron Devices, 2011, 58, 4384-4392.  | 1.6 | 23        |
| 102 | Scalable, highly stable Si-based metal-insulator-semiconductor photoanodes for water oxidation fabricated using thin-film reactions and electrodeposition. Nature Communications, 2021, 12, 3982.   | 5.8 | 23        |
| 103 | Observation of subsurface monolayer thickness fluctuations in InGa <sub>1-x</sub> GaN quantum wells by scanning capacitance microscopy and spectroscopy. Applied Physics Letters, 2004, 85, 407-409.  | 1.5 | 22        |
| 104 | Light scattering into silicon-on-insulator waveguide modes by random and periodic gold nanodot arrays. Journal of Applied Physics, 2009, 105, 073101.   | 1.1 | 22        |
| 105 | Nanoscale current transport in epitaxial SrTiO <sub>3</sub> on n <sup>+</sup> -Si investigated with conductive atomic force microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 2030. | 1.6 | 21        |
| 106 | Flexible, low-loss, large-area, wide-angle, wavelength-selective plasmonic multilayer metasurface. Journal of Applied Physics, 2013, 114, .   | 1.1 | 21        |
| 107 | Out-of-plane electromechanical coupling in transition metal dichalcogenides. Applied Physics Letters, 2020, 116, .  | 1.5 | 21        |
| 108 | Scanning tunneling microscopy and spectroscopy of Si/SiGe(001) superlattices. Applied Physics Letters, 1992, 61, 3166-3168.   | 1.5 | 20        |

| #   | ARTICLE   | IF  | CITATIONS |
|-----|---|-----|-----------|
| 109 | Ultra-stable 2D layered methylammonium cadmium trihalide perovskite photoelectrodes. Journal of Materials Chemistry C, 2018, 6, 11552-11560.  | 2.7 | 20        |
| 110 | Plasma-implanted Ti-doped hematite photoanodes with enhanced photoelectrochemical water oxidation performance. Journal of Alloys and Compounds, 2021, 870, 159376.  | 2.8 | 20        |
| 111 | Local conductivity and surface photovoltage variations due to magnesium segregation in p-type GaN. Journal of Applied Physics, 2004, 95, 6225-6231.   | 1.1 | 19        |
| 112 | Direct measurement and characterization of n+ superhalo implants in a 120 nm gate-length Si metal-oxide-semiconductor field-effect transistor using cross-sectional scanning capacitance microscopy. Applied Physics Letters, 2002, 81, 3993-3995.                                  | 1.5 | 18        |
| 113 | Integration of vertical InAs nanowire arrays on insulator-on-silicon for electrical isolation. Applied Physics Letters, 2008, 93, 203109.   | 1.5 | 18        |
| 114 | Atomic-scale structure of InAs/InAs <sub>1-x</sub> Sb <sub>x</sub> superlattices grown by modulated molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2940. | 1.6 | 17        |
| 115 | Miscut-angle dependence of perpendicular magnetic anisotropy in thin epitaxial CoPt <sub>3</sub> films grown on vicinal MgO. Applied Physics Letters, 2002, 81, 517-519.  | 1.5 | 17        |
| 116 | Scanning gate microscopy of InAs nanowires. Applied Physics Letters, 2007, 90, 233118.  | 1.5 | 17        |
| 117 | Increased InAs quantum dot size and density using bismuth as a surfactant. Applied Physics Letters, 2014, 105, .  | 1.5 | 17        |
| 118 | Commutativity of the GaAs/AlAs(100) band offset. Physical Review B, 1988, 38, 12764-12767.  | 1.1 | 16        |
| 119 | Effect of band mixing on hole-tunneling times in GaAs/AlAs double-barrier heterostructures. Physical Review B, 1992, 45, 3576-3582.   | 1.1 | 16        |
| 120 | Interfacial reactions and band offsets in the AlSb/GaSb/ZnTe material system. Physical Review B, 1992, 46, 13379-13388.   | 1.1 | 16        |
| 121 | Characterization of arsenide/phosphide heterostructure interfaces grown by gas-source molecular beam epitaxy. Applied Physics Letters, 1995, 67, 932-934.   | 1.5 | 16        |
| 122 | Charging effects in AlGaIn/GaN heterostructures probed using scanning capacitance microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2304.                               | 1.6 | 16        |
| 123 | Scanned electrical probe characterization of carrier transport behavior in InAs nanowires. Journal of Vacuum Science & Technology B, 2006, 24, 2036.  | 1.3 | 16        |
| 124 | Quantum state engineering with ultra-short-period (AlN) <sub>m</sub> /(GaN) <sub>n</sub> superlattices for narrowband deep-ultraviolet detection. Nanoscale, 2014, 6, 14733-14739.  | 2.8 | 16        |
| 125 | Subwavelength nanostructures integrated with polymer-packaged III-V solar cells for omnidirectional, broad-spectrum improvement of photovoltaic performance. Progress in Photovoltaics: Research and Applications, 2015, 23, 1398-1405.   | 4.4 | 16        |
| 126 | Transfer of patterned ion-cut silicon layers. Applied Physics Letters, 1998, 73, 2772-2774.   | 1.5 | 15        |



| #   | ARTICLE   | IF  | CITATIONS |
|-----|---|-----|-----------|
| 127 | Structural coloration with hourglass-shaped vertical silicon nanopillar arrays. <i>Optics Express</i> , 2018, 26, 30952.  | 1.7 | 15        |
| 128 | Epitaxy of Al films on GaN studied by reflection high-energy electron diffraction and atomic force microscopy. <i>Applied Physics Letters</i> , 1997, 70, 990-992.  | 1.5 | 14        |
| 129 | Cross-sectional scanning tunneling microscopy of GaAsSb/GaAs quantum well structures. <i>Journal of Applied Physics</i> , 2002, 92, 3761-3770.  | 1.1 | 14        |
| 130 | Large-area omnidirectional antireflection coating on low-index materials. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2013, 30, 2584.   | 0.9 | 14        |
| 131 | Interface structure in arsenide/phosphide heterostructure grown by gas-source MBE and low-pressure MOVPE. <i>Journal of Electronic Materials</i> , 1997, 26, 64-69.   | 1.0 | 13        |
| 132 | Local electronic properties of AlGaIn/GaN heterostructures probed by scanning capacitance microscopy. <i>Journal of Electronic Materials</i> , 2000, 29, 274-280.   | 1.0 | 13        |
| 133 | Voltage-controlled ferromagnetism and magnetoresistance in LaCoO <sub>3</sub> /SrTiO <sub>3</sub> heterostructures. <i>Journal of Applied Physics</i> , 2013, 114, .  | 1.1 | 13        |
| 134 | Wide-angle wavelength-selective multilayer optical metasurfaces robust to interlayer misalignment. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2013, 30, 27.  | 0.9 | 13        |
| 135 | Monolithic integration of perovskites on Ge(001) by atomic layer deposition: a case study with SrHf <sub>x</sub> Ti <sub>1-x</sub> O <sub>3</sub> . <i>MRS Communications</i> , 2016, 6, 125-132.   | 0.8 | 13        |
| 136 | Influence of the Substrate to the LSP Coupling Wavelength and Strength. <i>Nanoscale Research Letters</i> , 2018, 13, 280.  | 3.1 | 13        |
| 137 | A scanning tunneling microscopy study of atomic-scale clustering in InAsP/InP heterostructures. <i>Applied Physics Letters</i> , 1998, 72, 2135-2137.   | 1.5 | 12        |
| 138 | Polarization charges and polarization-induced barriers in Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN and In <sub>y</sub> Ga <sub>1-y</sub> N/GaN heterostructures. <i>Applied Physics Letters</i> , 2001, 79, 2916-2918.   | 1.5 | 12        |
| 139 | Scanning capacitance spectroscopy of an Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN heterostructure field-effect transistor structure: Analysis of probe tip effects. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002, 20, 1671. | 1.6 | 12        |
| 140 | Toward Cost-Effective Manufacturing of Silicon Solar Cells: Electrodeposition of High-Quality Si Films in a CaCl <sub>2</sub> -based Molten Salt. <i>Angewandte Chemie</i> , 2017, 129, 15274-15278.  | 1.6 | 12        |
| 141 | Growth Mechanisms and Morphology Engineering of Atomic Layer-Deposited WS <sub>2</sub> . <i>ACS Applied Materials &amp; Interfaces</i> , 2021, 13, 43115-43122.   | 4.0 | 12        |
| 142 | Commutativity of the GaAs/AlAs (100) band offset. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1989, 7, 391.   | 1.6 | 11        |
| 143 | Large peak-to-valley current ratios in triple barrier heterostructures. <i>Solid-State Electronics</i> , 1989, 32, 1095-1099.   | 0.8 | 11        |
| 144 | Semiconductor heterostructures and optimization of light-trapping structures for efficient thin-film solar cells. <i>Journal of Optics (United Kingdom)</i> , 2012, 14, 024007.   | 1.0 | 11        |

| #   | ARTICLE  | IF  | CITATIONS |
|-----|--|-----|-----------|
| 145 | Hyperspectral imaging for high-throughput, spatially resolved spectroscopic scatterometry of silicon nanopillar arrays. <i>Optics Express</i> , 2020, 28, 14209.   | 1.7 | 11        |
| 146 | Measurement of band offsets in Si/Si <sub>1-x</sub> Ge <sub>x</sub> and Si/Si <sub>1-x</sub> Ge <sub>x</sub> C <sub>y</sub> heterojunctions. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1997, 15, 1108. | 1.6 | 10        |
| 147 | Nanometer-scale compositional variations in III-V semiconductor heterostructures characterized by scanning tunneling microscopy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1999, 17, 2246-2250.  | 0.9 | 10        |
| 148 | Long Time-Constant Trap Effects in Nitride Heterostructure Field Effect Transistors. <i>Materials Research Society Symposia Proceedings</i> , 2000, 622, 6281.   | 0.1 | 10        |
| 149 | Demonstration and analysis of reduced reverse-bias leakage current via design of nitride semiconductor heterostructures grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2006, 99, 014501.   | 1.1 | 10        |
| 150 | Cross-sectional scanning thermal microscopy of ErAs/GaAs superlattices grown by molecular beam epitaxy. <i>Nanotechnology</i> , 2015, 26, 265701.  | 1.3 | 10        |
| 151 | Cost-effective liquid-junction solar devices with plasma-implanted Ni/TiN/CNF hierarchically structured nanofibers. <i>Journal of Electroanalytical Chemistry</i> , 2021, 887, 115167.   | 1.9 | 10        |
| 152 | Wafer-Scale Synthesis of WS <sub>2</sub> Films with In Situ Controllable p-Type Doping by Atomic Layer Deposition. <i>Research</i> , 2021, 2021, 9862483.  | 2.8 | 10        |
| 153 | Negative differential resistance due to resonant interband tunneling of holes. <i>Journal of Applied Physics</i> , 1990, 68, 3744-3746.  | 1.1 | 9         |
| 154 | Characterization of CdSe/ZnTe heterojunctions. <i>Journal of Crystal Growth</i> , 1991, 111, 820-822.  | 0.7 | 9         |
| 155 | Nanoscale Characterization of Materials. <i>MRS Bulletin</i> , 1997, 22, 17-21.  | 1.7 | 9         |
| 156 | Improvement of performance of InAs quantum dot solar cell by inserting thin AlAs layers. <i>Nanoscale Research Letters</i> , 2011, 6, 83.  | 3.1 | 9         |
| 157 | Computational analysis of thin film InGaAs/GaAs quantum well solar cells with back side light trapping structures. <i>Optics Express</i> , 2012, 20, A864.   | 1.7 | 9         |
| 158 | A Low-Leakage Epitaxial High- $\kappa$ Gate Oxide for Germanium Metal-Oxide-Semiconductor Devices. <i>ACS Applied Materials &amp; Interfaces</i> , 2016, 8, 5416-5423.   | 4.0 | 9         |
| 159 | Probing nanoscale variations in strain and band structure of $\text{MoS}_2$ on Au nanopyramids using tip-enhanced Raman spectroscopy. <i>Physical Review B</i> , 2018, 97, .   | 1.1 | 9         |
| 160 | Crystalline SrZrO <sub>3</sub> deposition on Ge (001) by atomic layer deposition for high- $\kappa$ dielectric applications. <i>Journal of Applied Physics</i> , 2018, 124, .  | 1.1 | 9         |
| 161 | Band structure effects in interband tunnel devices. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1991, 9, 2405.   | 1.6 | 8         |
| 162 | Atomic-scale compositional structure of InAsP/InP and InNAsP/InP heterostructures grown by molecular-beam epitaxy. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1998, 16, 2395.                           | 1.6 | 8         |

| #   | ARTICLE   | IF  | CITATIONS |
|-----|---|-----|-----------|
| 163 | Cross-sectional scanning tunneling microscopy of InAsSb/InAsP superlattices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1781.  | 1.6 | 8         |
| 164 | Quantitative analysis of nanoscale electronic properties in an Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN heterostructure field-effect transistor structure. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1671. | 1.6 | 8         |
| 165 | Localized variations in electronic structure of AlGaIn/GaN heterostructures grown by molecular-beam epitaxy. Applied Physics Letters, 2001, 79, 2749-2751.  | 1.5 | 8         |
| 166 | Observation of In concentration variations in InGaIn/GaN quantum-well heterostructures by scanning capacitance microscopy. Applied Physics Letters, 2005, 86, 202113.   | 1.5 | 8         |
| 167 | Ultraviolet and solar-blind spectral imaging with subwavelength transmission gratings. Applied Physics Letters, 2009, 95, 161107.   | 1.5 | 8         |
| 168 | Quantitative scanning thermal microscopy of ErAs/GaAs superlattice structures grown by molecular beam epitaxy. Applied Physics Letters, 2013, 102, .  | 1.5 | 8         |
| 169 | Effect of particle size distribution on near-field thermal energy transfer within the nanoparticle packings. Journal of Photonics for Energy, 2019, 9, 1.   | 0.8 | 8         |
| 170 | Measurement of the MgSe/Cd <sub>0.54</sub> Zn <sub>0.46</sub> Se valence band offset by X-ray photoelectron spectroscopy. Journal of Crystal Growth, 1994, 138, 508-512.  | 0.7 | 7         |
| 171 | Analysis of interface electronic structure in In <sub>x</sub> Ga <sub>1-x</sub> N/GaN heterostructures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 2169.   | 1.6 | 7         |
| 172 | Characterization of nanoscale electronic structure in nonpolar GaN using scanning capacitance microscopy. Journal of Applied Physics, 2008, 103, .  | 1.1 | 7         |
| 173 | Fabrication of birefringent nanocylinders for single-molecule force and torque measurement. Nanotechnology, 2014, 25, 235304.   | 1.3 | 7         |
| 174 | Angular dependence of light trapping in In <sub>0.3</sub> Ga <sub>0.7</sub> As/GaAs quantum-well solar cells. Journal of Applied Physics, 2014, 115, 044303.  | 1.1 | 7         |
| 175 | Strain and Hole Gas Induced Raman Shifts in Ge <sub>1-x</sub> Si <sub>x</sub> /Ge <sub>1-x</sub> Core-Shell Nanowires Using Tip-Enhanced Raman Spectroscopy. Nano Letters, 2015, 15, 4303-4310.   | 4.5 | 7         |
| 176 | Integration of subwavelength optical nanostructures for improved antireflection performance of mechanically flexible GaAs solar cells fabricated by epitaxial lift-off. Solar Energy Materials and Solar Cells, 2015, 143, 567-572.   | 3.0 | 7         |
| 177 | <title>Novel InAs/GaSb/AlSb tunnel structures</title>. , 1990, 1283, 2.   |     | 6         |
| 178 | Interband tunneling in InAs/GaSb/AlSb heterostructures. Journal of Crystal Growth, 1991, 111, 664-668.  | 0.7 | 6         |
| 179 | Scanning tunneling microscopy and spectroscopy of Si-based heterostructures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1993, 11, 1149.  | 1.6 | 6         |
| 180 | Electronic properties of Si/Si <sub>1-x</sub> Ge <sub>x</sub> /C <sub>y</sub> heterojunctions. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1639.  | 1.6 | 6         |

| #   | ARTICLE   | IF  | CITATIONS |
|-----|---|-----|-----------|
| 181 | Influence of the dipole interaction energy on clustering in $\text{In}_x\text{Ga}_{1-x}\text{N}$ alloys. Applied Physics Letters, 2001, 78, 2303-2305.  | 1.5 | 6         |
| 182 | Influence of AlN buffer on electronic properties and dislocation microstructure of AlGaIn/GaN grown by molecular beam epitaxy on SiC. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1818. | 1.6 | 6         |
| 183 | Defects in nitride semiconductors: From nanoscale imaging to macroscopic device behavior. Materials Science in Semiconductor Processing, 2006, 9, 308-314.  | 1.9 | 6         |
| 184 | Peak splitting and locking behavior arising from Fano interference between localized surface plasmons and cavity modes. Physical Review B, 2019, 99, .  | 1.1 | 6         |
| 185 | Composition-dependent structural transition in epitaxial $\text{Bi}_x\text{Sb}_{1-x}$ thin films on Si(111). Physical Review Materials, 2019, 3, .  | 0.9 | 5         |
| 186 | Microstructural properties of superlattices and $\text{InAs}_x\text{Sb}_{1-x}$ ordered alloys grown by modulated molecular beam epitaxy. Journal of Crystal Growth, 1997, 175-176, 833-837.   | 0.7 | 5         |
| 187 | Characterization and analysis of a novel hybrid magnetoelectronic device for magnetic field sensing. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 1834-1837.   | 0.9 | 5         |
| 188 | Analysis of local carrier modulation in InAs semiconductor nanowire transistors. Journal of Vacuum Science & Technology B, 2007, 25, 1427.  | 1.3 | 5         |
| 189 | Scanning capacitance microscopy of ErAs nanoparticles embedded in GaAs pn junctions. Applied Physics Letters, 2011, 99, .   | 1.5 | 5         |
| 190 | Highly improved passivation of c-Si surfaces using a gradient $\text{a-Si:H}$ layer. Journal of Applied Physics, 2018, 123, .   | 1.1 | 5         |
| 191 | Cross-sectional scanning tunneling microscopy of MBE-grown Si p-n junctions and Si/SiGe superlattices. Journal of Crystal Growth, 1993, 127, 435-439.   | 0.7 | 4         |
| 192 | P2-induced exchange on GaAs during gas-source molecular beam epitaxy growth interruptions. Journal of Crystal Growth, 1996, 164, 77-83.   | 0.7 | 4         |
| 193 | Deep-level transient spectroscopy of Si/Si $\alpha$ $\beta$ GexCy heterostructures. Applied Physics Letters, 1998, 73, 647-649.   | 1.5 | 4         |
| 194 | Determination of thermal parameters of one-dimensional nanostructures through a thermal transient method. Journal of Thermal Analysis and Calorimetry, 2009, 97, 1023-1026.   | 2.0 | 4         |
| 195 | Conductivity and structure of ErAs nanoparticles embedded in GaAs pn junctions analyzed via conductive atomic force microscopy. Applied Physics Letters, 2012, 100, 233117.   | 1.5 | 4         |
| 196 | Minimized open-circuit voltage reduction in GaAs/InGaAs quantum well solar cells with bandgap-engineered graded quantum well depths. Applied Physics Letters, 2014, 105, 123906.  | 1.5 | 4         |
| 197 | Strain-dependent luminescence and piezoelectricity in monolayer transition metal dichalcogenides. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2020, 38, 042205.  | 0.6 | 4         |
| 198 | Omnidirectional Current Enhancement From Laminated Moth-Eye Textured Polymer Packaging for Large-Area, Flexible III-V Solar Modules. IEEE Journal of Photovoltaics, 2021, 11, 685-691.  | 1.5 | 4         |

| #   | ARTICLE   | IF  | CITATIONS |
|-----|---|-----|-----------|
| 199 | A monolithic field-effect-transistor-amplified magnetic field sensor. Applied Physics Letters, 1999, 75, 731-733.   | 1.5 | 3         |
| 200 | Proximal probe characterization of nanoscale charge transport properties in Co/SiO <sub>2</sub> multilayer structures. Journal of Electronic Materials, 2000, 29, 1299-1303.  | 1.0 | 3         |
| 201 | Scanning capacitance characterization of potential screening in InAs nanowire devices. Journal of Applied Physics, 2009, 105, .   | 1.1 | 3         |
| 202 | Influence of surface treatment and interface layers on electrical spin injection efficiency and transport in InAs. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, 1164-1168.                | 0.6 | 3         |
| 203 | Ballistic transport and electrical spin signal enhancement in a nanoscale three-terminal spintronic device. Applied Physics Letters, 2011, 98, 142115.  | 1.5 | 3         |
| 204 | Resistive switching of SiOX with one diode-one resistor nanopillar architecture fabricated via nanosphere lithography. , 2014, , .  |     | 3         |
| 205 | Electromagnetic Thermal Energy Transfer in Nanoparticle Assemblies Below Diffraction Limit. Journal of Thermal Science and Engineering Applications, 2021, 13, .  | 0.8 | 3         |
| 206 | Electronic structure of epitaxially grown and regrown GaN pn junctions characterized by scanning Kelvin probe and capacitance microscopy. Journal of Applied Physics, 2022, 131, .  | 1.1 | 3         |
| 207 | Distinguishing negatively-charged and highly conductive dislocations in gallium nitride using scanning Kelvin probe and conductive atomic force microscopy. Materials Research Society Symposia Proceedings, 2002, 743, L2.4.1.         | 0.1 | 2         |
| 208 | Evidence for coherent interaction between quantum well states in triple barrier heterostructures. Superlattices and Microstructures, 1990, 8, 455-458.  | 1.4 | 1         |
| 209 | Cross-sectional scanning tunneling microscopy of mixed-anion semiconductor heterostructures. Micron, 1999, 30, 51-58.   | 1.1 | 1         |
| 210 | Frequency Response of Trap States in an Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN Heterostructure Field-Effect Transistor Measured at the Nanoscale by dC/dV Spectroscopy. Materials Research Society Symposia Proceedings, 2001, 680, 1. | 0.1 | 1         |
| 211 | Dependence of local electronic structure in p-type GaN on crystal polarity and presence of inversion domain boundaries. Journal of Vacuum Science & Technology B, 2006, 24, 245.  | 1.3 | 1         |
| 212 | Engineering of plasmonic effects in photodetectors and high-efficiency photovoltaics. , 2010, , .   |     | 1         |
| 213 | Toward high-efficiency quantum dot solar cells: optimized gratings for ultrathin waveguide devices. Proceedings of SPIE, 2010, , .  | 0.8 | 1         |
| 214 | (Invited) Resistive Switching Characteristics and Controllable Quantized Conductance in Single-Crystal Anatase TiO <sub>2</sub> on Si (001). ECS Transactions, 2014, 64, 147-152.   | 0.3 | 1         |
| 215 | Epitaxy: A Chemical Route to Monolithic Integration of Crystalline Oxides on Semiconductors (Adv.) Tj ETQq1 1 0.784314 rgBT /Overloc  | 1.9 | 1         |
| 216 | Uncertainty Analysis of Near-Field Thermal Energy Transfer within Nanoparticle Packing. , 2018, , .   |     | 1         |

| #   | ARTICLE  | IF  | CITATIONS |
|-----|--|-----|-----------|
| 217 | Measurement of the strain dependence of the Si/Ge (100) valence band offset. , 1990, , .   |     | 0         |
| 218 | Characterization of arsenide/phosphide heterostructure interfaces by scanning tunneling microscopy. Applied Surface Science, 1996, 104-105, 522-528.   | 3.1 | 0         |
| 219 | An atomic-scale view of semiconductor heterostructures using scanning tunneling microscopy. , 0, , .   |     | 0         |
| 220 | Analysis of localized charge trapping behavior in AlGaIn/GaN heterostructures. , 0, , .  |     | 0         |
| 221 | I-V characteristics of polarization-induced barriers in AlGaIn/GaN heterostructures. , 0, , .  |     | 0         |
| 222 | Imaging of thickness and compositional fluctuations in InGaIn <sup>x</sup> GaN quantum wells by scanning capacitance microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1808. | 1.6 | 0         |
| 223 | Scanning Capacitance Characterization of Potential Screening in InAs Nanowire Devices. , 2008, , .   |     | 0         |
| 224 | Optimal Control over the InAs Nanowire Growth for System Integration and their Structural and Transport Properties. , 2008, , .  |     | 0         |
| 225 | Coupling of light scattered by nanoparticles into waveguide modes in quantum-well solar cells. , 2008, , .   |     | 0         |
| 226 | Determination of Thermal Parameters of Nanostructures Exhibiting One-Dimensional Heat Flow Through a Thermal Transient Method. Materials Research Society Symposia Proceedings, 2009, 1172, 54.  | 0.1 | 0         |
| 227 | Tunneling MOSFETs Based on III-V Staggered Heterojunctions. Materials Research Society Symposia Proceedings, 2010, 1252, 4.  | 0.1 | 0         |
| 228 | A green campus project and advances in semiconductor nanostructures for photovoltaic applications. , 2012, , .   |     | 0         |
| 229 | Performance benefits for thin film solar cells incorporating semiconductor heterostructures and light trapping. , 2012, , .  |     | 0         |
| 230 | Mechanical Stability of Mononucleosome Revealed by Optical Torque Wrench. Biophysical Journal, 2013, 104, 580a.  | 0.2 | 0         |
| 231 | Integrated optical nanostructures for wide-angle antireflection and light trapping in III/V solar cells. , 2014, , .   |     | 0         |
| 232 | Photoelectrochemical characterization of p-type CH <sub>3</sub> NH <sub>3</sub> PM <sub>3</sub> perovskite. , 2016, , .  |     | 0         |
| 233 | Large Area Nanostructure Integration for Broad-Spectrum, Omnidirectional Antireflection Improvements on Polymer Packaged, Mechanically Flexible, Epitaxial Lift-Off III-V Solar Cells. , 2017, , .   |     | 0         |
| 234 | Large Area Nanostructure Integration for Broad-Spectrum, Omnidirectional Antireflection Improvements on Polymer Packaged, Mechanically Flexible, Epitaxial Lift-off III-V Solar Arrays. , 2018, , .  |     | 0         |

| #   | ARTICLE  | IF | CITATIONS |
|-----|--|----|-----------|
| 235 | Tip-enhanced Raman spectroscopy of semiconductor nanostructures. , 2017, , . |    | 0         |